



High efficiency, high-side switch with extended diagnostics and smart driving for capacitive loads







Product status link
IPS2050H
IPS2050H-32
IPS2050HQ
IPS2050HQ-32



Features

- 8 V to 60 V operating supply voltage range
- Operating output current: 2.4 A (IPS2050H/HQ) or 5.6 A (IPS2050H-32/HQ-32) per channel
- · Smart driving of capacitive load
- Fast demagnetization of inductive loads
- Under-voltage lock-out
- V_{CC} over-voltage protection
- Per-channel overload and over-temperature protection
- Case over-temperature protection
- Ground disconnection protection
- Per channel overload/over-temperature event diagnostic pins
- Designed to meet IEC 61000-4-2, IEC 61000-4-4, IEC 61000-4-5
- Packages: PowerSSO-24 and QFN48L 8x6x0.9 mm

Applications

- Programmable logic control
- Vending machines
- Industrial PC peripheral input/output
- Numerical control machines
- General high-side switch applications

Description

The IPS2050H/HQ and IPS2050H-32/HQ-32 are dual high-side switch ICs able to drive capacitive, resistive or inductive loads with one side connected to ground.

The very low R_{DS-ON} (\leq 50 m Ω up to T_J = 125 °C) makes the IC suitable for applications with up to 2.4 A (IPS2050H/HQ) or 5.6 A (IPS2050H-32/HQ-32) steady state operating current.

Each output channel is independently protected against junction over-temperature events by a junction temperature sensor, and a further temperature sensor is included to monitor case temperature, so an overheated output channel can only be turned back ON when the case temperature returns below the reset temperature.

The embedded per-channel overload protection circuit monitors the output current and, on triggering of the activation threshold (I_{PK-X}), starts modulating the impedance of the output switch to limit the output current to I_{LIM-X} , for both IC and load protection.

The IC offers two different sets of activation threshold and limitation levels (I_{PKH-X} , I_{LIMH-X} and I_{PKL-X} , I_{LIML-X}) for smart driving of capacitive loads (such as bulb lamps) and loads with initial peak current requirements.

The IC diagnostics is based on two FAULT pins (current source), one for each channel. Each FAULT pin is activated by an overload or an over-temperature event on the related channel.



1 Block diagram

UNDERVOLTAGE LOCKOUT **V_{CC} CLAMP** FLT_X **OUTPUT CLAMP** CONTROL IN_{x} LOGIC **CURRENT LIMITATION →**OUT_x **JUNCTION TEMP** I_{PDX} **DETECTION** R_{PD} **x2 x2 CASE TEMP DETECTION GND**

Figure 1. IPS2050H/HQ, IPS2050H-32/HQ-32 block diagram

DS13779 - Rev 4 page 2/37



2 Pin connection

Figure 2. Pin connections (top through view)

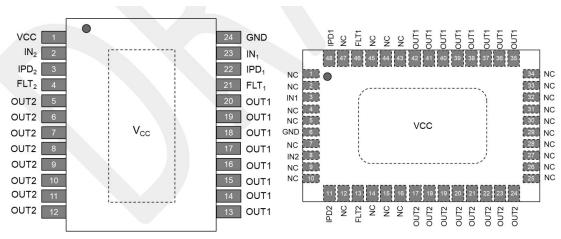


Table 1. Pin descriptions

Pin	no.	News	Beautifut			
PSSO24	QFN48L	Name	Description			
1, exposed pad	exposed pad	V _{CC}	Supply voltage			
2	8	IN ₂	Channel 2 input			
			Channel 2 initial current duration / level selector.			
			Connect to GND by a capacitor to set duration of I_{PKH-2} (see Section 7.3 and Table 9 / Table 10).			
3	11	IPD ₂	Connect to IN $_2$ by a 220 k Ω resistor to disable initial I $_{PKH-2}$ threshold on channel 2 (the over-current limit for channel 2 is only I $_{PKL-2}$).			
			Connect to GND by a 10 k Ω resistor to disable I _{PKL-2} on channel 2 (the over-current threshold for channel 2 is only I _{PKH-2}).			
4	13	FLT ₂	Fault (Overload or Over-temperature) diagnostic pin for channel 2			
5 to 12	17 to 24	OUT ₂	Channel 2 power stage output			
3 10 12	17 10 24	0012	Short the pins on the same net of the application board			
13 to 20	35 to 42	OUT ₁	Channel 1 power stage output			
	00 10 12	33.1	Short the pins on the same net of the application board			
21	46	FLT ₁	Fault (Overload or Over-temperature) diagnostic pin for channel 1			
			Channel 1 initial current duration / level selector.			
			Connect to GND by a capacitor to set duration of I _{PKH-1} (see Section 7.3 and Table 9 / Table 10).			
22	48	IPD ₁	Connect to IN ₁ by a 220 k Ω resistor to disable initial I _{PKH-1} threshold on channel 1 (the over-current limit for channel 1 is only I _{PKL-1}).			
			Connect to GND by a 10 k Ω resistor to disable I _{PKL-1} on channel 1 (the over-current threshold for channel 1 is only I _{PKH-1}).			
23	3	IN ₁	Channel 1 input			
24	6	GND	Device ground			

DS13779 - Rev 4 page 3/37



Piı	Pin no.		Description			
PSSO24	QFN48L	Name	Description			
-	1 to 5; 7 to 10; 12; 14 to 16; 25 to 34; 43 to 45; 47	NC	Internally not connected. If necessary, these pins can be routed in the application.			

Note: Leaving IPD $_X$ floating is equivalent to a 1 μ s duration for I $_{PKH-X}$.

DS13779 - Rev 4 page 4/37



3 Absolute maximum ratings

Absolute maximum ratings are the values beyond which damage to the device may occur. Functional operation under these conditions is not implied. All voltages are referenced to GND.

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.3 to 65	V
I _{CC}	Maximum DC reverse current (from GND to V _{CC})	-250	mA
I _{OUT}	Output stage current	Internally limited	Α
-lout	Reverse current (from OUT to V _{CC})	5	Α
V _{IN}	IN pin voltage	-0.3 to V _{CC}	V
I _{IN}	IN pin current	-10/+10	mA
V _{PD}	I _{PD} pin voltage	-0.3 to 5.5	V
I _{PD}	I _{PD} pin current	-1/+10	mA
V _{FAULT}	FLT pins voltage	-0.3 to 5.5	V
I _{FAULT}	FLT pins current	-1 ⁽¹⁾ /+10	mA
E	Single pulse avalanche energy, two channels driven simultaneously	1.3(2)	J
E _{AS}	(T _{AMB} = 125 °C, V _{CC} = 24 V, I _{OUT} = 2 A)	1.0 ⁽³⁾	J
P _{TOT}	Power Dissipation at T _C = 25 °C	Internally limited	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Junction Operating Temperature	Internally limited	°C
T _C	Case Operating Temperature	-40 to 150	°C

^{1.} intended as worst case when IC is in normal operation (no fault)

DS13779 - Rev 4 page 5/37

^{2.} IPS2050H / IPS2050H-32

^{3.} IPS2050HQ/IPS2050HQ-32



4 Thermal data

Table 3. Thermal data

Symbol	Parameter	PSSO24	QFN48L	Unit
R _{th(JC)} ⁽¹⁾	Thermal resistance junction-case per channel	0.7	1	°C/W
R _{th(JA)} ⁽²⁾	Thermal resistance junction-ambient	22	26	°C/W

^{1.} Rth between the die and the bottom case surface measured by cold plate as per JESD51.

DS13779 - Rev 4 page 6/37

^{2.} JESD51-7.



5 Electrical characteristics

(8 V < V $_{CC}$ < 60 V; -40 °C < T $_{J}$ < 125 °C, unless otherwise specified)

Table 4. Supply

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V_{UVON}	Under-voltage ON threshold	-	6.9	-	8	V
V _{UVOFF}	Under-voltage OFF threshold	-	6.5	-	7.8	V
V _{UVH}	Under-voltage hysteresis	-	0.15	0.5	-	V
I _{SOFF}	Supply current in OFF state	$IN_X = GND$, $OUT_X = open load$	-	0.5	0.95	mA
		V _{CC} = 24V	1.95	2.6	3.2	mA
I _{SON}	Supply current in ON state	V _{CC} = 36V	2.05	- 8 - 7.8 0.5 - 0.5 0.95 2.6 3.2 2.7 3.3	mA	
		V _{CC} = 60V	2.25	2.9	3.5	mA

Table 5. Output stage

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
R _{DSON}	On-state resistance	$V_{CC} = 24 \text{ V}, R_{LOAD} = 12 \Omega,$ @ $T_J = 25 ^{\circ}\text{C}$	-	25	30	mΩ
KDSON	On-state resistance	V_{CC} = 24 V, R_{LOAD} = 12 Ω , @ T_{J} = 125 °C	-	-	50	mΩ
V _{OUT(OFF)}	OFF state output voltage	V _{IN} = 0 V, I _{OUT} = 0 A	-	-	2	V
I _{OUT(OFF)}	OFF state output current	V _{IN} = 0 V, V _{OUT} = 0 V	-	-	10	μΑ

Table 6. Switching

(V_{CC} = 24 V; -40 °C < T_J < 125 °C, R_{LOAD} = 12 Ω , input rise time < 0.1 μ s)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
t _r	Rise time		-	25	50	μs
t _f	Fall time		-	15	30	μs
t _{PD(L-H)}	Propagation delay time IN to OUT, low to high			14	25	μs
t _{PD(H-L)}	Propagation delay time IN to OUT, high to low		-	33	60	μs
t _{D(VCCON)}	Propagation delay time IN to OUT at power-on	$V_{IN} = V_{CC}$ and rising from 0 to 24 V	150	500	1600	μs

DS13779 - Rev 4 page 7/37





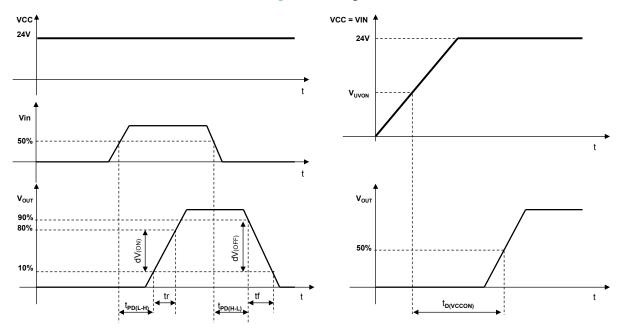


Table 7. Input pin (IN1 or IN2)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
V _{IL}	Input pin low level voltage	-	-	-	0.8	V
V _{IH}	Input pin high level voltage	-	2.2	-	-	V
V _{I(HYST)}	Input pin hysteresis voltage	-	-	0.4	-	V
L		V _{IN} = V _{CC} = 36V	-	-	200	
IIN	Input pin current	V _{IN} = V _{CC} = 60V	-	-	- \\ - \\ 200	μA

Table 8. Diagnostic pins (FLT₁, FLT₂)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
IH _{FLT}	Diagnostic pins source current in fault condition.	V _{FLT} = 1 V (fault condition active)	-2	-3	-4	mA
FLI	Diagnostic pins source current in fault condition.	$V_{FLT} = 5 V$ (fault condition active)	-0.4	-0.7	-1.0	ША
IL _{FLT}	Diagnostic pins leakage current	Normal operation V _{CC} = 60 V	-	-	-25	μA
BT _{FLT}	Diagnostic pins blanking time	-	60	-	400	μs
VCL _{FLT}	Diagnostic pins clamp voltage	I _{FLT} = +1 mA	6	6.8	8	V
VOLFLI	Diagnostic pins clamp voltage	I _{FLT} = -1 mA	-	-	0.7	'

DS13779 - Rev 4 page 8/37



Table 9. IPS2050H/HQ overload protections

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Overload	with Dual Threshold Protection: I_{PD} pin to GND by C_{PD} (4	70 pF ≤ C _{PD} ≤ 470	nF); se	ee Section 7.3.1		
I _{PKH-X}	Initial overcurrent activation threshold for channel x		-	11.5	-	Α
I _{LIMH-X}	Initial overcurrent limitation level for channel x		6.1	8.8	11.5	Α
D _{PKX}	Time limit of Initial overcurrent for channel x		-	215*C _{PD} [nF]	-	μs
I _{PKL-X}	Steady state overcurrent activation threshold for channel x	V _{CC} = 24 V	-	5.2	-	Α
I _{LIML-X}	Steady state overcurrent limitation level for channel x		2.5	3.5	4.5	Α
I _{HYS}	Steady state output Current limitation hysteresis	ed to IN by 10kΩ resolved $V_{CC} = 24 \text{ V}$	-	0.3	-	Α
I _{LIML-OFF}	Steady state overcurrent limitation deactivation threshold		-	I _{LIML} - I _{HYS}	-	Α
Overload	with Single Level (Lowest) Protection: I _{PD} pin connected	to IN by 10kΩ resi	stor; s	ee Section 7.3.	2	
I _{PKL-X}	Steady state overcurrent activation threshold for channel x		-	5.2	-	Α
I _{LIML-X}	Steady state overcurrent limitation level for channel x	\/ - 24\/	2.5	3.5	4.5	Α
I _{HYS}	Steady state output Current limitation hysteresis	V _{CC} = 24 V	-	0.3	-	Α
I _{LIML-OFF}	Steady state overcurrent limitation deactivation threshold		-	I _{LIML} -I _{HYS}	-	Α
Overload	with Single Level (Highest) Protection: I _{PD} pin connected	to GND by 10kΩ r	esisto	r; see Section 7	7.3.3.	
I _{PKH-X}	Initial overcurrent activation threshold for channel x	\/ - 24\/	-	11.5	-	Α
I _{LIMH-X}	Initial overcurrent limitation level for channel x	V _{CC} = 24 V	6.1	8.8	11.5	Α

Table 10. IPS2050H-32/HQ-32 overload protections

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Uni
Overload	with Dual Threshold Protection: I_{PD} pin to GND by C_{PD} (4)	70 pF ≤ C _{PD} ≤ 470	nF); se	ee Section 7.3.1		
I _{PKH-X}	Initial overcurrent activation threshold for channel x		-	19.8	-	Α
I _{LIMH-X}	Initial overcurrent limitation level for channel x		12.5	17.9	23.2	Α
D _{PKX}	Time limit of Initial overcurrent for channel x		-	215*C _{PD} [nF]	-	μs
I _{PKL-X}	Steady state overcurrent activation threshold for channel x	V _{CC} = 24 V	-	10.5	-	Α
I _{LIML-X}	Steady state overcurrent limitation level for channel x		5.7	8.0	10.4	Α
I _{HYS}	Steady state output Current limitation hysteresis		-	0.3	-	Α
I _{LIML-OFF}	Steady state overcurrent limitation deactivation threshold		-	I _{LIML} - I _{HYS}	-	Α
Overload	with Single Level (Lowest) Protection: I _{PD} pin connected	to IN by 10kΩ resi	stor; s	ee Section 7.3.	2	
I _{PKL-X}	Steady state overcurrent activation threshold for channel x		-	10.5	-	Α
I _{LIML-X}	Steady state overcurrent limitation level for channel x	V _{CC} = 24 V	5.7	8.0	10.4	Α
I _{HYS}	Steady state output Current limitation hysteresis	V _{CC} = 24 V	-	0.3	-	Α
I _{LIML-OFF}	Steady state overcurrent limitation deactivation threshold		-	I _{LIML} -I _{HYS}	-	Α
Overload	with Single Level (Highest) Protection: I _{PD} pin connected	to GND by 10kΩ r	esisto	r; see Section 7	7.3.3.	
I _{PKH-X}	Initial overcurrent activation threshold for channel x	\/ - 24\/	-	19.8	-	Α
I _{LIMH-X}	Initial overcurrent limitation level for channel x	V _{CC} = 24 V	12.5	17.9	23.2	Α

DS13779 - Rev 4 page 9/37



Figure 4. High (left) and Low (right) I_{LOAD} control activation thresholds (I_{PK}) and limitation levels (I_{LIM})

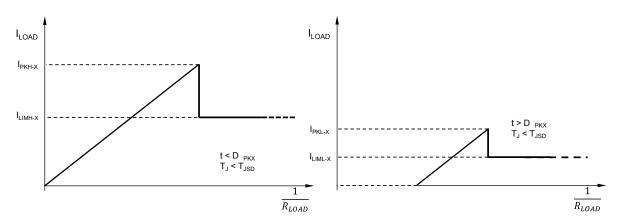


Table 11. Other protections

Symbol	Parameter	Min.	Тур.	Max.	Unit	
Overtemp	erature protections					
T _{JSD}	Junction temperature shutdown	-	150	170	190	°C
T_{JR}	Junction temperature reset	-	-	150	-	°C
T _{JHYS}	Junction temperature hysteresis	-	7	20	-	°C
T _{CSD}	Case temperature shutdown	-	-	130	-	°C
T _{CR}	Case temperature reset	-	-	110	-	°C
T _{CHYS}	Case temperature hysteresis	-	-	20	-	°C
Ground d	isconnection/Wire break					
I _{LGND}	GND disconnection output current	V _{INX} = Vcc = 24 V, V _{OUT} = 0 V	-	-	0.5	mA
VCC over	voltage			,		
V _{CLAMP}	V _{CC} Clamp Voltage	I _{CC} ≤ 10 mA	65.5	70.0	73.5	V
Demagne	tization of inductive load					
V_{DEMAG}	Demagnetization Voltage	I _{OUT} = 0.5 A, Load ≥ 10 mH	Vcc-76	Vcc-72.5	Vcc-68	V

DS13779 - Rev 4 page 10/37



6 Output Logic

Table 12. Output stage truth table

(L=pin voltage Low, H=pin voltage High, X=not determined)

	IN _X	OUT _X	FLT _X
Normal Operation	L	L	L
	H	H	L
Overload	L	L	L
	H	X ⁽¹⁾	H
Junction over-temperature	L	L	L
	H	L	H
Case over-temperature	L	L	L
	H	L ⁽²⁾	H ⁽²⁾
UVLO	L	L	X
	H	L	X

- 1. Pin voltage = $I_{OUT} * R_{LOAD}$
- 2. Channels with $T_J > T_{JSD}$ are forced off and the related FLT are activated

Logic Side Supply MCU_INX VCC OUT1

Process Side Supply

MCU_FLTX X2

Process Side Supply

Figure 5. Typical application diagram with opto-couplers

DS13779 - Rev 4 page 11/37



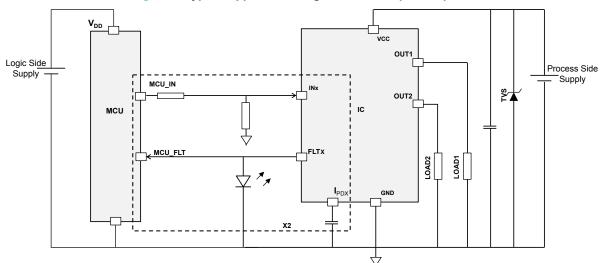


Figure 6. Typical application diagram without opto-couplers

DS13779 - Rev 4 page 12/37



7 Protections and diagnostic

The IC integrates several protections to help the design of robust applications.

7.1 Under-voltage lock-out

The IC is turned off if the voltage on V_{CC} pin falls below the turn-off threshold (V_{UVOFF}). Normal operation restarts after V_{CC} exceeds the turn-on threshold (V_{UVON}). Turn-on and turn-off thresholds are defined in Table 4.

7.2 Over-temperature

The device is protected against overheating in case of overload conditions. During the driving period (when the MCU is forcing the IN_X pin high), if the output is overloaded, the device suffers two different thermal stresses, one related to the junction temperature of each output channel, and the other related to the whole case temperature. The two thermal faults (Thermal Junction and Thermal Case) have different trigger thresholds: T_{JSD} and T_{CSD} , respectively.

Usually, in thermal stress conditions due to overload, the junction thermal shutdown is the first protection that is activated: each output channel (OUT_X) is turned off when its junction temperature (T_{JX}) is higher than the activation threshold (T_{JSD}) and turned back on when it goes below the reset threshold (T_{JR}). This behavior continues while overload on the output persists. When the thermal protection is active for OUT_X , the related FLT_X (current source) becomes active accordingly.

If the thermal protection is active and the temperature of the case (T_C) increases over the case protection threshold (T_{CSD}) , then the thermal case protection is activated and the output is switched off until the junction temperature of each channel in fault and case temperature fall below the respective reset thresholds (T_{CR}) and T_{JR} . The FLT_X pins are active even when thermal case events occur.

Figure 7 shows the thermal protection behavior, while Figure 8 and Figure 9 show typical temperature trends and output vs. input state.

DS13779 - Rev 4 page 13/37

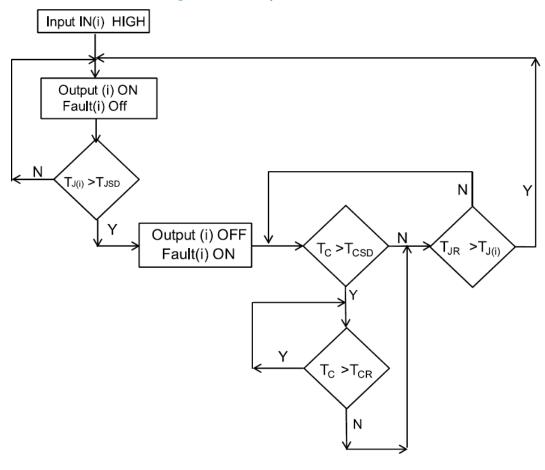
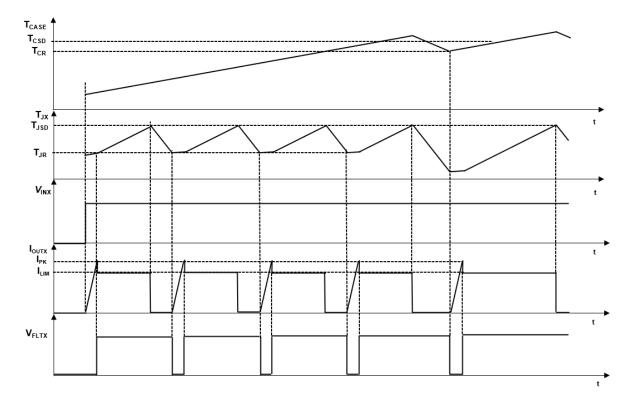


Figure 7. Thermal protection flowchart





DS13779 - Rev 4 page 14/37

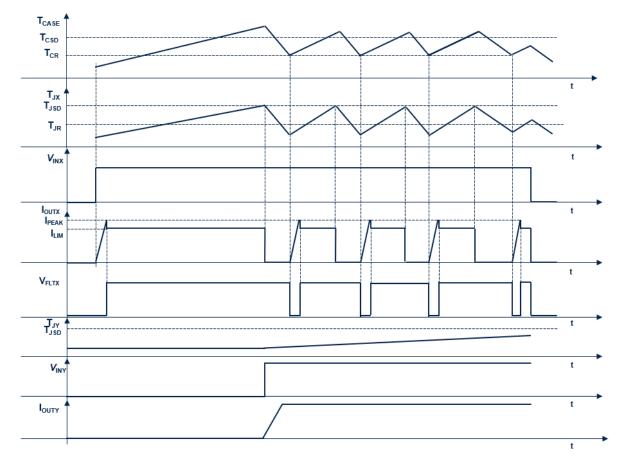


Figure 9. Thermal protection plot, $T_C > T_{CSD}$

7.3 Overload

The IC integrates two independent overload protection circuits (one for each output channel) consisting of an output current sensing section and an output current limitation section.

When the output channel is ON, the sensing circuitry monitors the current supplied to the load: if the activation threshold (I_{PK-X}) is triggered, then the current limitation control circuitry is activated to limit output current to the current limitation level (I_{LIM-X}) and FLT_X pin is activated until the overload condition is removed.

The IC allows the user to set both single and dual activation thresholds for each channel. See the following sections for details and Table 9 / Table 10 for specific activation thresholds and limitation levels.

Note that while an output channel operates below its activation threshold, the power dissipation can be calculated by $R_{ON} * I_{OUT}^2$, but when the current limitation circuit is activated, power dissipation increases and can be calculated by $V_{DS} * I_{LIM-X}$, where V_{DS} is the voltage drop between OUT_X and V_{CC} pins of the IC. In order to protect the IC against thermal stress, the overtemperature protection is always active and retains the highest priority.

7.3.1 Overload protection with dual threshold

This case is activated when the pin I_{PDX} is connected to GND by a capacitor (C_{PD}) and the IC works with two activation thresholds I_{PKH-X} and I_{PKL-X} .

The I_{PKH-X} is active only in the limited time frame between the L-H transition of the IN_X signal and the D_{PKX} delay defined by the following design rule:

$$D_{PKX}[\mu s] = 215 \times CPD[nF]$$

The above design rule is valid in the range 470 pF \leq C_{PD} \leq 470 nF (see Table 9 / Table 10).

If the I_{PKH-X} is triggered within the D_{PKX} time frame, then the output current is limited to I_{LIMH-X} .

After DPKX has elapsed, the IC operates with IPKL-X activation threshold and ILIML-X limitation level, respectively.

DS13779 - Rev 4 page 15/37

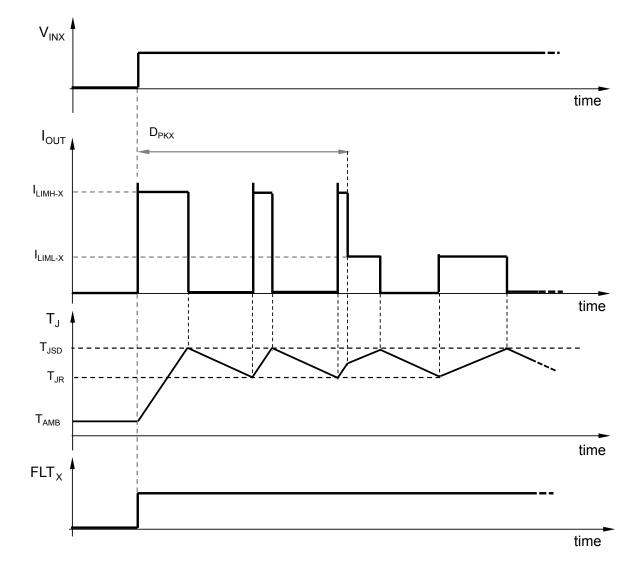


Figure 10. Short-circuit behavior with dual threshold (T_{CASE} < T_{CSD})

7.3.2 Overload protection with single (low) threshold

The user can set the activation threshold to I_{PKL-X} and the limitation level to I_{LIML-X} by connecting the I_{PDX} pin to the related IN_X pin with a 220 K Ω resistor.

This condition is equivalent to setting $D_{PKX} = 0 \mu s$.

Note: Leaving I_{PDX} floating is equivalent to having an initial peak duration of 1 μ s.

7.3.3 Overload protection with single (high) threshold

The user can set the activation threshold to I_{PKH-X} and the limitation level to I_{LIMH-X} by connecting the I_{PDX} pin to GND with a 10 K Ω resistor.

7.4 V_{CC} disconnection protection

 V_{CC} disconnection involves the disconnection of the module from the supply line. When this condition is detected, the output channel can be driven normally until the voltage on VCC pin remains higher than the UVLO threshold. In case of inductive load, if the V_{CC} is disconnected while the channel is active, the energy stored in the inductance is discharged through the power switch thanks to the integrated demagnetization circuit.

DS13779 - Rev 4 page 16/37



7.5 GND disconnection protection

GND disconnection is the disconnection of the module from the reference line. When this condition occurs, the output channel is turned off regardless of the input status.

When this event occurs, the IC continues working normally until the voltage between VCC and GND pins of the IC results \geq V_{UVOFF}. The voltage on the GND pin of the IC rises up to the supply rail voltage level. In case of a GND disconnection event, a current (I_{LGND}) flows through OUT pin.

For an inductive load, if the GND is disconnected while the output channel is active, the current flows through the power, which is activated by an active clamp as if the input had been deactivated.

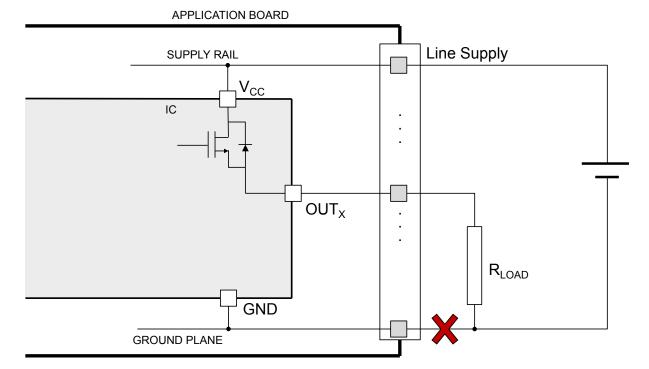


Figure 11. Ground disconnection

DS13779 - Rev 4 page 17/37



8 Active clamp

Active clamp is also known as Fast Demagnetization of inductive loads or Fast Current Decay. When a high-side driver turns off an inductance, an under-voltage on output is detected.

The OUT pin is pulled-down to V_{CC} - V_{DEMAG} . The conduction state is modulated by an internal circuitry in order to keep the OUT pin voltage at $\sim V_{DEMAG}$ until the load energy has been dissipated. The energy is dissipated in both IC internal switch and load resistance.

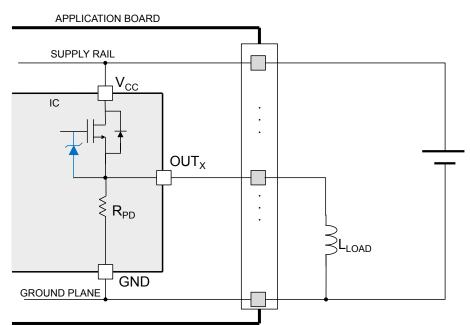
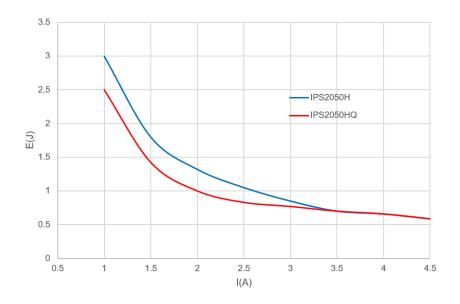


Figure 12. Active clamp equivalent principle schematic

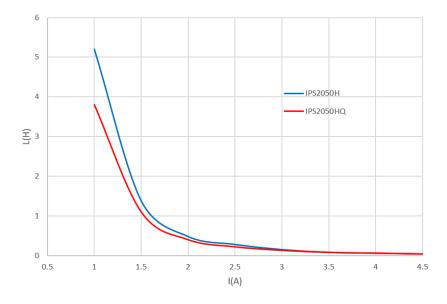
Figure 13. Typical demagnetization: E vs I (single pulse, two channels driven simultaneously) at V_{CC} = 24 V and T_{AMB} = 125 °C



DS13779 - Rev 4 page 18/37



Figure 14. Typical demagnetization: L vs I (single pulse, two channels driven simultaneously) at V_{CC} = 24 V and T_{AMB} = 125 °C



DS13779 - Rev 4 page 19/37



9 Package information

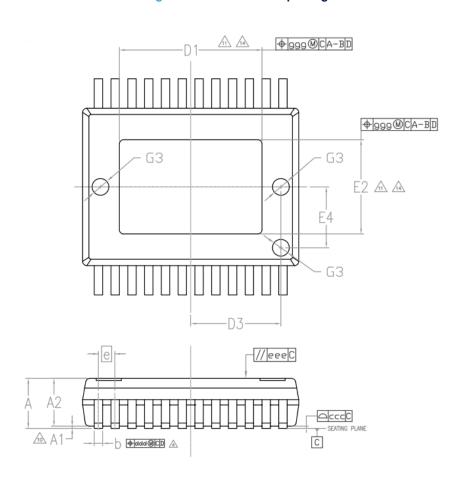
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

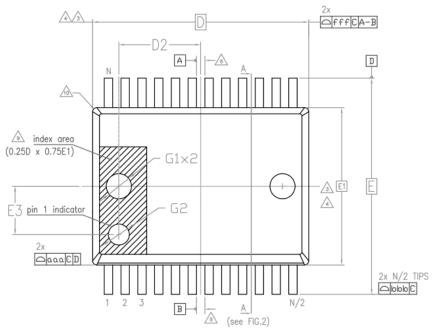
DS13779 - Rev 4 page 20/37



9.1 Package mechanical data

Figure 15. PowerSSO-24 package dimensions





DS13779 - Rev 4 page 21/37



Figure 16. PowerSSO-24 package, section A-A

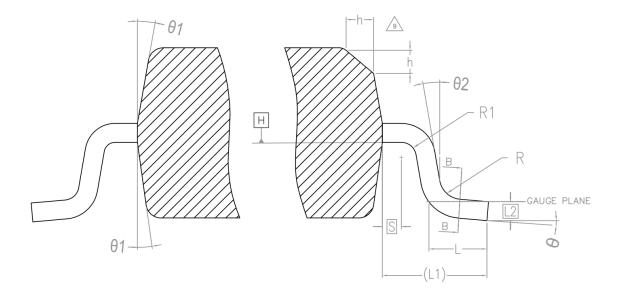
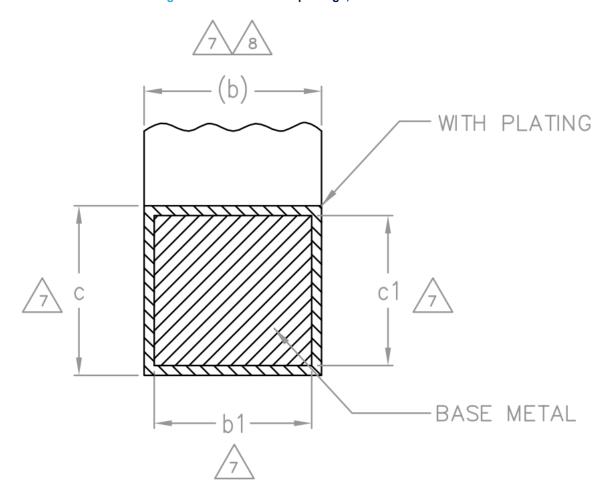


Figure 17. PowerSSO-24 package, section B-B



DS13779 - Rev 4 page 22/37



Table 13. PowerSSO-24 mechanical data

Country I	[mm]			
Symbol	Min.	Nom.	Max.	
θ	0°	-	7°	
Θ1	5°	-	10°	
Θ2	0°	-	-	
А	-	-	2.42	
A1	0.005	-	0.09	
A2	2.23	2.28	2.33	
b	0.375	-	0.45	
b1	-	0.40	-	
С	0.24	-	0.30	
c1	0.20	0.20	0.30	
D		10.30 BSC	'	
D1	6.60	-	7.00	
D2	-	3.65	-	
D3	-	4.30	-	
е		0.80 BSC		
E	10.30 BSC			
E1	7.50 BSC			
E2	4.60 - 5.0		5.00	
E3	-	2.30	-	
E4	-	2.90	-	
G1	-	1.20	-	
G2	-	1.00	-	
G3	-	0.80	-	
h	0.30	-	0.40	
L	0.60	0.70	0.85	
L1	1.40 REF			
L2	0.25 BSC			
N	24			
R	0.30	-	-	
R1	0.20	-	-	
S	0.25	-	-	

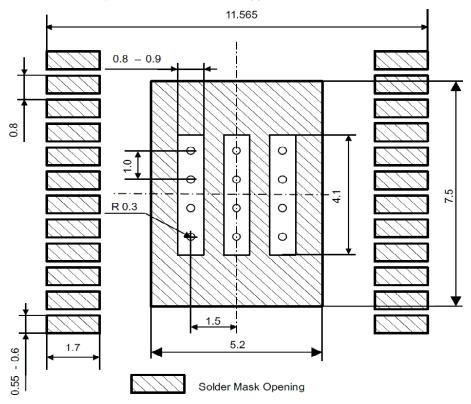
DS13779 - Rev 4 page 23/37



Table 14. Tolerance of forms and positions

Symbol	Tolerance of forms and positions
aaa	0.20
bbb	0.20
ccc	0.10
ddd	0.20
eee	0.10
fff	0.20
999	0.15

Figure 18. PowerSSO-24 suggested footprint [mm]

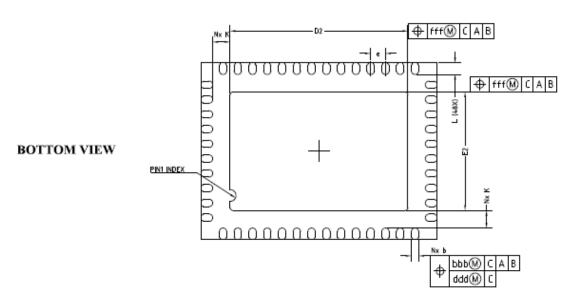


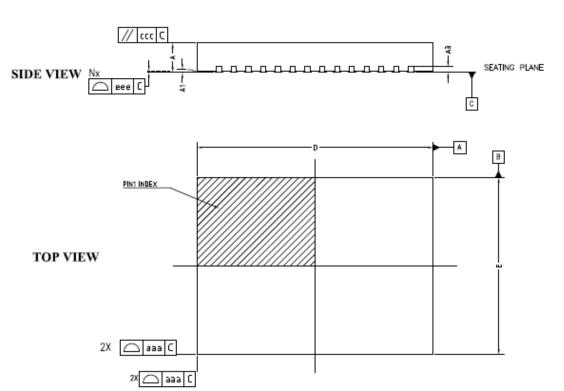
STMicroelectronics is not responsible for PCB-related issues. The footprint shown in the above figure is a suggestion which may differ from the customer PCB supplier design rules.

DS13779 - Rev 4 page 24/37



Figure 19. QFN48L package dimensions





DS13779 - Rev 4 page 25/37



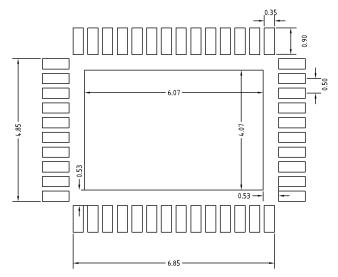
Table 15. QFN48L mechanical data

Symbol -	[mm]			
	Min.	Nom.	Max.	
A	0.80	0.85	0.90	
A1	0.00	-	0.05	
А3	0.20 REF.			
b	0.20 0.25 0.30		0.30	
D	8.00 BSC			
е	0.50 BSC			
E	6.00 BSC			
D2	5.97	6.02	6.07	
E2	3.97	4.02	4.07	
L	0.365	0.40	0.435	
k	0.53	-	-	
N	48			

Table 16. Tolerance of forms and positions

Symbol	Tolerance of forms and positions
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.05
eee	0.08
fff	0.10

Figure 20. QFN48L suggested footprint [mm]



DS13779 - Rev 4 page 26/37



10 Packing information

10.1 Packing mechanical data

Figure 21. PowerSSO-24 tube shipment (no suffix)

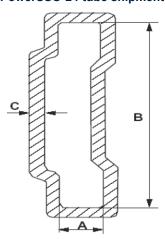


Table 17. PowerSSO-24 tube shipment information

All dimensions are in mm

Description	Value
Base quantity	49
Bulk quantity	1225
Tube length (±0.5)	532
Α	3.5
В	13.8
C (±0.1)	0.6

DS13779 - Rev 4 page 27/37



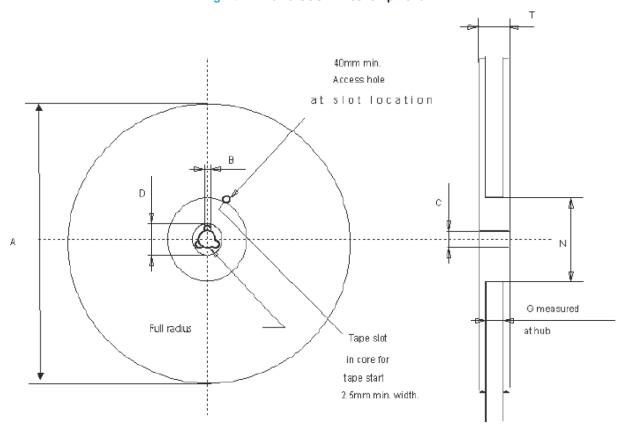


Figure 22. PowerSSO-24 reel shipment

Table 18. PowerSSO-24 reel information

All dimensions are in mm

Description	Value
Base quantity	1000
Bulk quantity	1000
A (max.)	330
B (min.)	1.5
C (±0.2)	13
F	20.2
G (2 ±0)	24.4
N (min.)	100
T (max.)	30.4

DS13779 - Rev 4 page 28/37



Р1 D TOP COVER TAPE Ρ User Direction of Feed Start Тор No components Components No components cover 500mm min tape Empty components pockets 500mm min saled with cover tape. User direction of feed 0 0 0 0 0 ₫ User Direction of Feed

Figure 23. PowerSSO-24 tape drawings

Table 19. PowerSSO-24 tape dimension

All dimensions are in mm

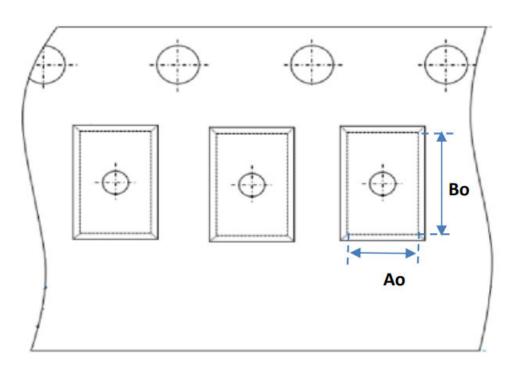
Description	Symbol	Value
Tape width	W	24
Tape hole spacing	P0 (± 0.1)	4
Component spacing	Р	12
Hole diameter	D (± 0.05)	1.55
Hole diameter	D1 (min.)	1.5
Hole position	F (± 0.1)	11.5
Compartment depth	K (max.)	2.85
Hole spacing	P1 (± 0.1)	2

Note: According to the Electronic Industries Association (EIA) standard 481 rev. A, Feb 1986.

DS13779 - Rev 4 page 29/37



Figure 24. QFN48L reel shipment reference



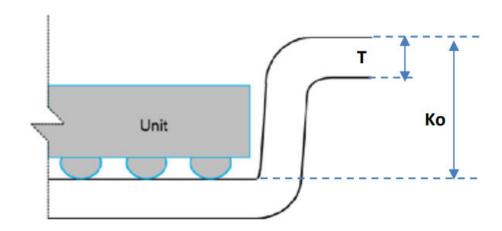


Table 20. Standard SPC parameters

Item	Description
Ao	Pocket Length
Во	Pocket Width
Ko	Pocket Depth
Т	Tape Thickness

DS13779 - Rev 4 page 30/37



Figure 25. QFN48L carrier tape dimensions

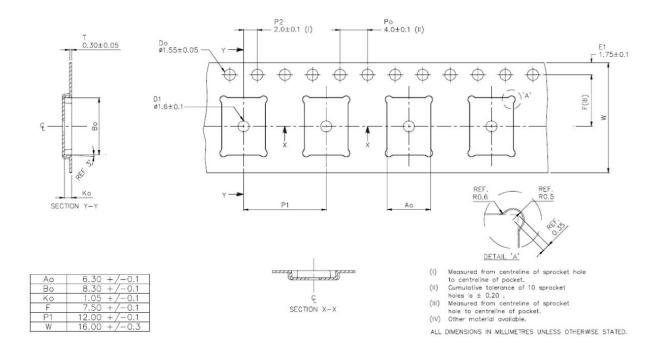
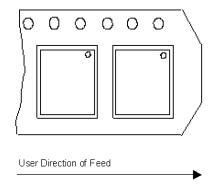


Figure 26. QFN48L carrier tape, Pin 1 indication



DS13779 - Rev 4 page 31/37



11 Ordering information

Table 21. Ordering information

Part number	Package	Packaging	
IPS2050H	IPS2050H		
IPS2050HTR	PowerSSO-24	Tape and reel	
IPS2050H-32	F0Wel330-24	Tube	
IPS2050HTR-32		Tape and reel	
IPS2050HQ	OFN48L 8x6x0.9 mm	Tana and roal	
IPS2050HQ-32	QFN40L 0X0XU.9 IIIIII	Tape and reel	

DS13779 - Rev 4 page 32/37



Revision history

Table 22. Document revision history

Date	Version	Changes
15-Nov-2021	1	Initial release.
02-Dec-2021	2	Changed I _{SOFF} max. value in Table 4.
01-Aug-2022	3	Add QFN data: fig.2, 12, 15, 16, 20, 21, 22; tables 1, 2, 3, 14, 15, 19, 20. Divided table 9 in tables 9, 10, 11. Some minor changes.
26-Apr-2023	4	Modified Table 1; corrected Table 12; changed Figure 8 and Figure 9; add Figure 14. Changed Figure 15 and Table 13; add Figure 16 and Figure 17; some minor changes.

DS13779 - Rev 4 page 33/37



Contents

1	Bloc	k diagr	ram	2	
2	Pin connection				
3	Absolute maximum ratings				
4	Ther	mal da	nta	6	
5	Elec	trical c	haracteristics	7	
6	Output Logic				
7	Protections and diagnostic				
	7.1	Under	r-voltage lock-out	13	
	7.2	Over-t	temperature	13	
	7.3	Overlo	oad	15	
		7.3.1	Overload protection with dual threshold	15	
		7.3.2	Overload protection with single (low) threshold	16	
		7.3.3	Overload protection with single (high) threshold	16	
	7.4	$V_{CC} d$	lisconnection protection	16	
	7.5	GND (disconnection protection	17	
8	Activ	ve clam	np		
9	Package information				
	9.1 Package mechanical data				
10	Pack	king inf	formation		
	10.1	Packir	ng mechanical data	27	
11	Orde	ering in	nformation		
Rev	ision	history	/		



List of figures

Figure 1.	IPS2050H/HQ, IPS2050H-32/HQ-32 block diagram	2
Figure 2.	Pin connections (top through view)	3
Figure 3.	Timing	8
Figure 4.	High (left) and Low (right) I_{LOAD} control activation thresholds (I_{PK}) and limitation levels (I_{LIM})	0
Figure 5.	Typical application diagram with opto-couplers	1
Figure 6.	Typical application diagram without opto-couplers	2
Figure 7.	Thermal protection flowchart	4
Figure 8.	Thermal protection plot, T _J > T _{JSD}	4
Figure 9.	Thermal protection plot, T _C > T _{CSD}	5
Figure 10.	Short-circuit behavior with dual threshold (T _{CASE} < T _{CSD})	6
Figure 11.	Ground disconnection	7
Figure 12.	Active clamp equivalent principle schematic	8
Figure 13.	Typical demagnetization: E vs I (single pulse, two channels driven simultaneously) at V _{CC} = 24 V and T _{AMB} = 125 °C	
Figure 14.	Typical demagnetization: L vs I (single pulse, two channels driven simultaneously) at V_{CC} = 24 V and T_{AMB} = 125	,
	°C	
Figure 15.	PowerSSO-24 package dimensions	
Figure 16.	PowerSSO-24 package, section A-A	
Figure 17.	PowerSSO-24 package, section B-B	
Figure 18.	PowerSSO-24 suggested footprint [mm]	4
Figure 19.	QFN48L package dimensions	
Figure 20.	QFN48L suggested footprint [mm]	
Figure 21.	PowerSSO-24 tube shipment (no suffix)	
Figure 22.	PowerSSO-24 reel shipment	
Figure 23.	PowerSSO-24 tape drawings	
Figure 24.	QFN48L reel shipment reference	
Figure 25.	QFN48L carrier tape dimensions	
Figure 26.	QFN48L carrier tape, Pin 1 indication	1

DS13779 - Rev 4 page 35/37





List of tables

Table 1.	Pin descriptions	. 3
Table 2.	Absolute maximum ratings	. 5
Table 3.	Thermal data	. 6
Table 4.	Supply	. 7
Table 5.	Output stage	. 7
Table 6.	Switching	. 7
Table 7.	Input pin (IN1 or IN2)	. 8
Table 8.	Diagnostic pins (FLT ₁ , FLT ₂)	. 8
Table 9.	IPS2050H/HQ overload protections	. 9
Table 10.	IPS2050H-32/HQ-32 overload protections	. 9
Table 11.	Other protections	10
Table 12.	Output stage truth table	11
Table 13.	PowerSSO-24 mechanical data	23
Table 14.	Tolerance of forms and positions	24
Table 15.	QFN48L mechanical data	26
Table 16.	Tolerance of forms and positions	26
Table 17.	PowerSSO-24 tube shipment information	
Table 18.	PowerSSO-24 reel information	28
Table 19.	PowerSSO-24 tape dimension	29
Table 20.	Standard SPC parameters	30
Table 21.	Ordering information	32
Table 22.	Document revision history	33

DS13779 - Rev 4 page 36/37



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DS13779 - Rev 4 page 37/37